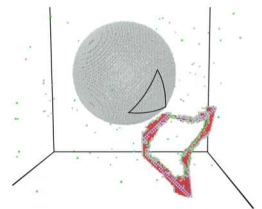
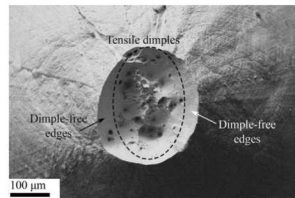
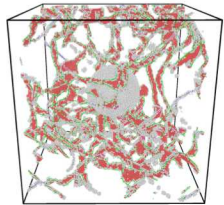




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# Void Growth by Dislocation Adsorption During Ductile Rupture



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## The Standard Theory of Ductile Rupture

Ductile rupture = failure by. microvoid coalescence

Three steps:

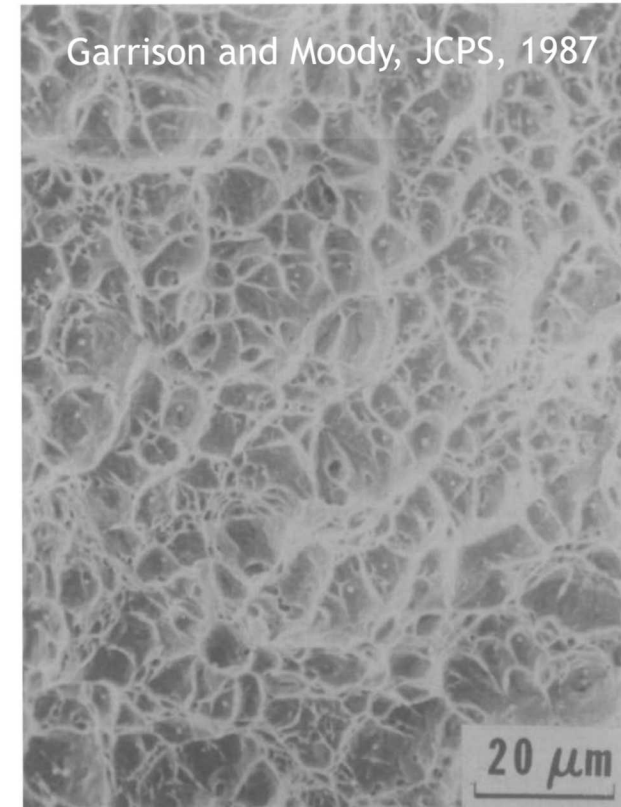
1. Voids nucleate at “inclusions” or other hard particles
2. Void grow via plastic deformation
  - Grow rate typically described in terms of Rice-Tracey

$$\frac{\dot{R}}{R} = \alpha \exp \left( \frac{3\sigma^H}{2\sigma_Y} \right) \dot{\epsilon}^{eq}$$

3. Rupture occurs when microvoids coalesce

Wildly successful, but still outstanding questions and unexplained observations:

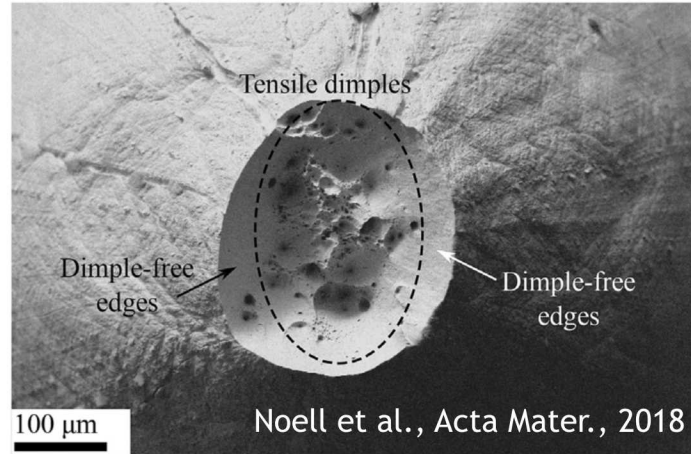
- How do voids nucleate in pure metals?
- How do voids nucleate in shear-dominated loading?
- What micromechanical processes underlie void growth? How do we expect the micromechanics of growth to affect the rupture process?



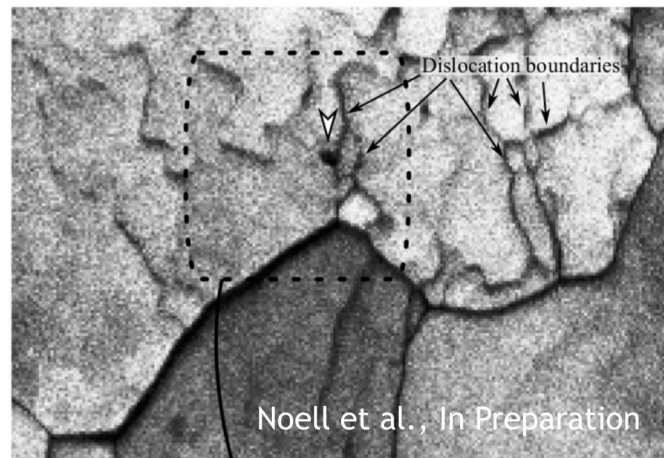
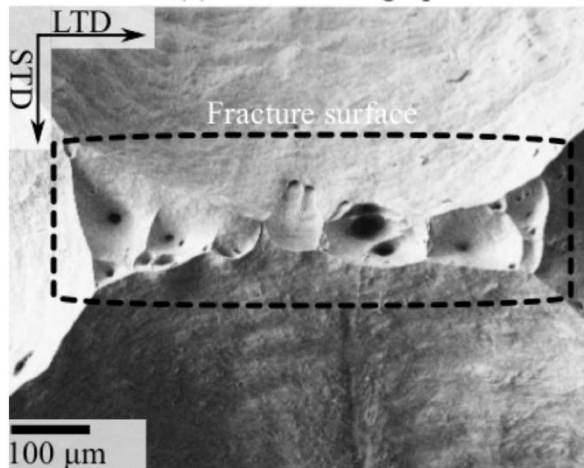


# Void nucleation in pure metals

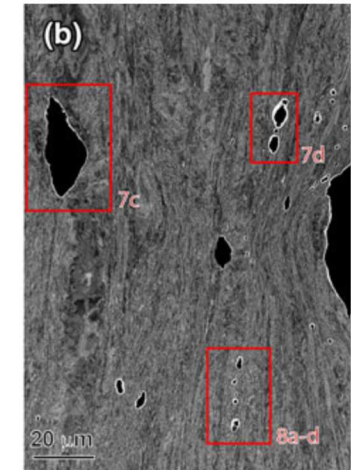
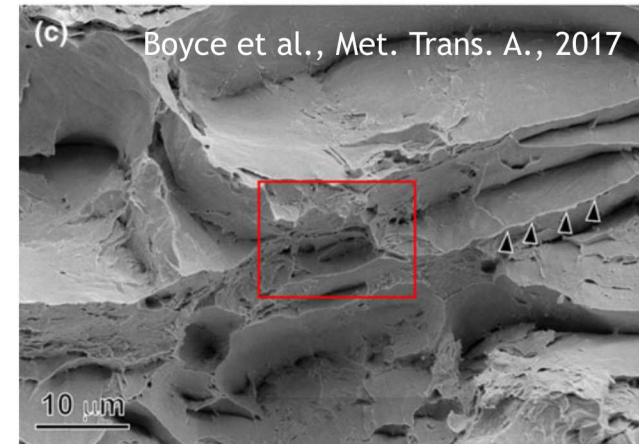
99.999% Cu



99.99% Al

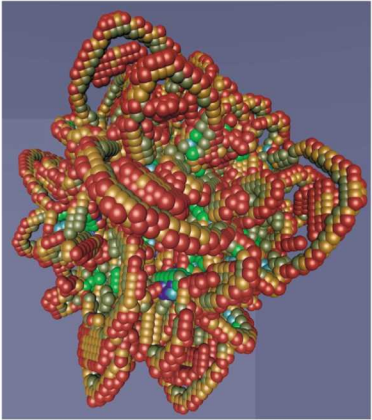


99.9% Ta

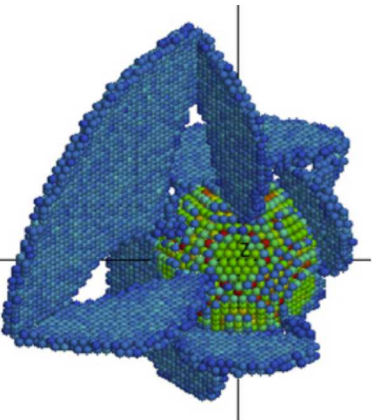


*Consistent feature:* voids tend to nucleate at dislocation boundaries/cell walls, but not those with the high misorientation

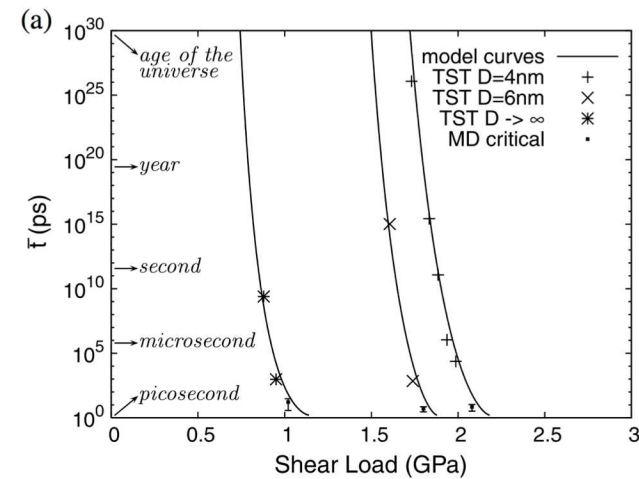
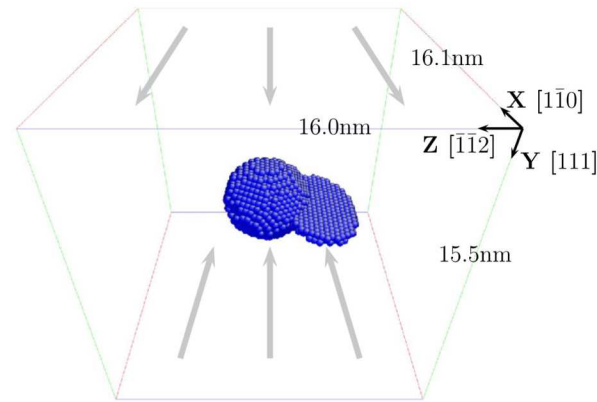
# Micromechanics of void growth



Marian et al., PRL, 2004



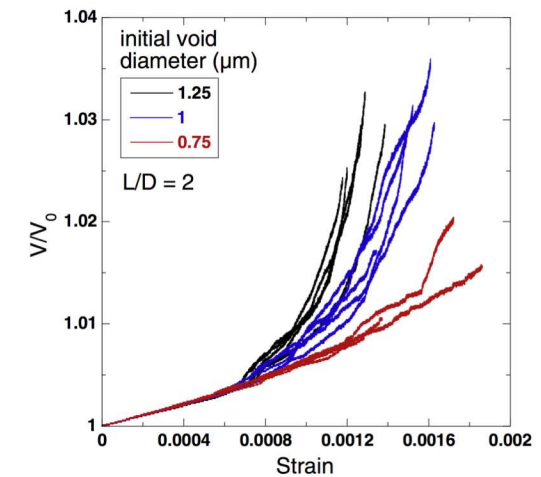
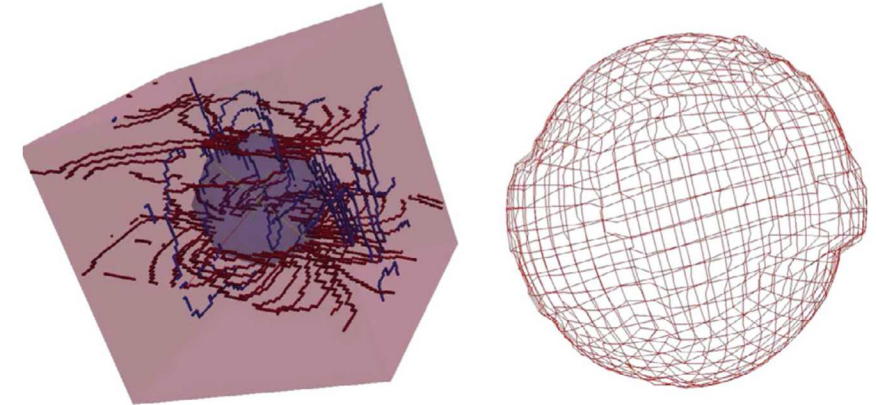
Bringa et al., Acta Mater., 2010



Nguyen and Warner, PRL, 2012

Only relevant for high stress loading!

Dislocation nucleation



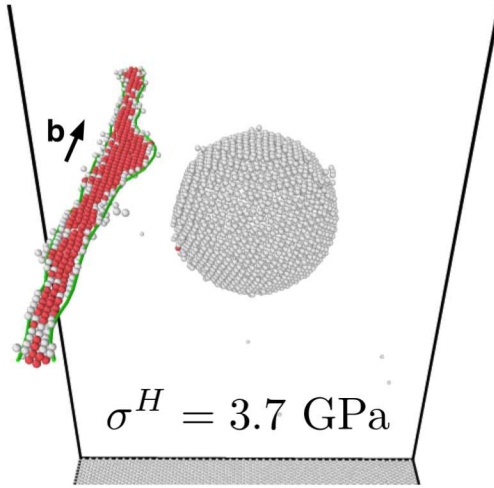
Dislocation adsorption

*Major outstanding questions:*

- Fundamental dislocation-void interactions?
- Relationship to nucleation-mediated growth?
- Growth rate as a function of stress?

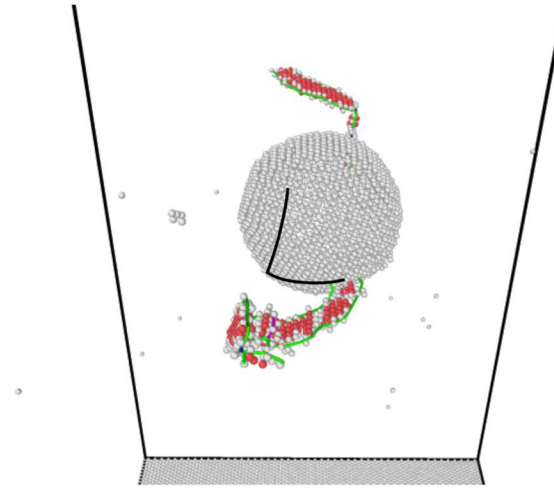


# Dislocation-void interactions under hydrostatic stress

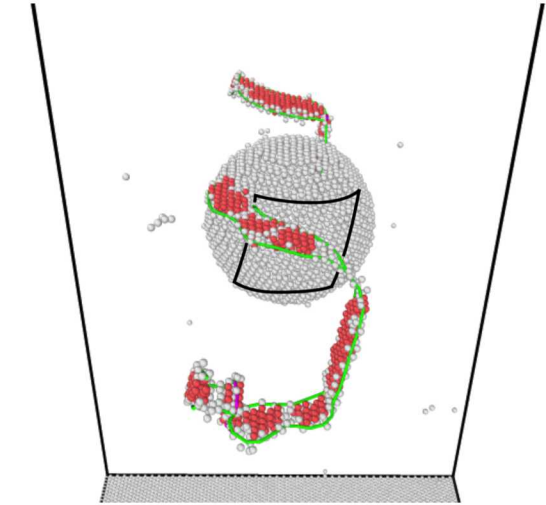


Screw dislocation in FCC Al

No volume change to insert a screw dislocation!



Glides, cross-slips, glides,...



...cross-slips, glides, cross-slips...

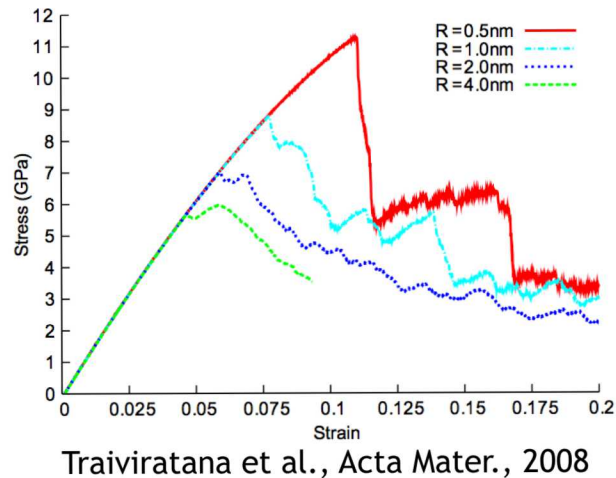
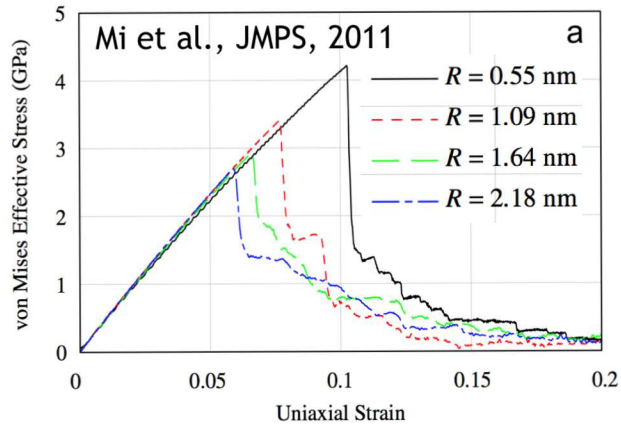
$$\delta V = \int_S \mathbf{b} \cdot d\mathbf{A}$$

Hirth and Lothe, 1992  
Bulatov et al., Scripta Mater., 2010

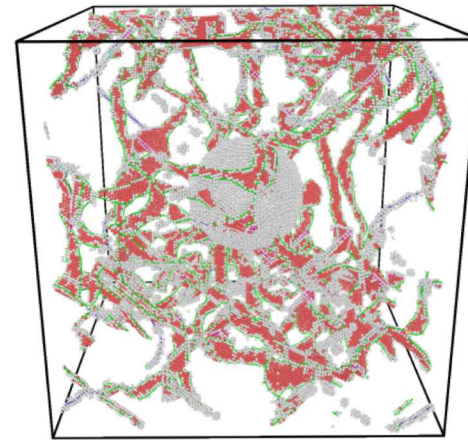
Growth is controlled by glide and cross-slip of pre-existing dislocations

- Enables growth without high stresses

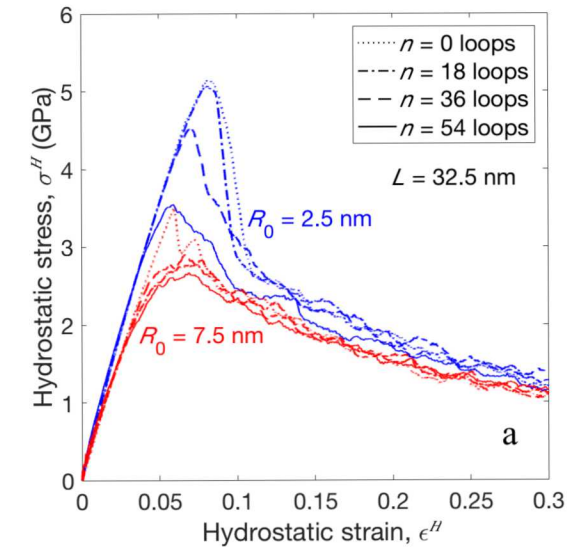
## No pre-existing dislocations



## Initial configuration



18 loops  $\approx 3.8 \times 10^{16} \text{ m}^{-2}$



Stress drop associated with dislocation nucleation goes away as the initial dislocation density increases

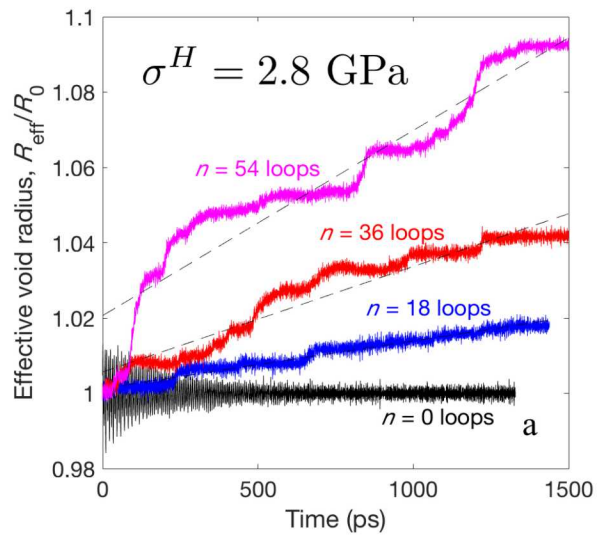
- Post-yield, results converge together...

Even when system is initially dislocation-free, growth is controlled by dislocation adsorption!

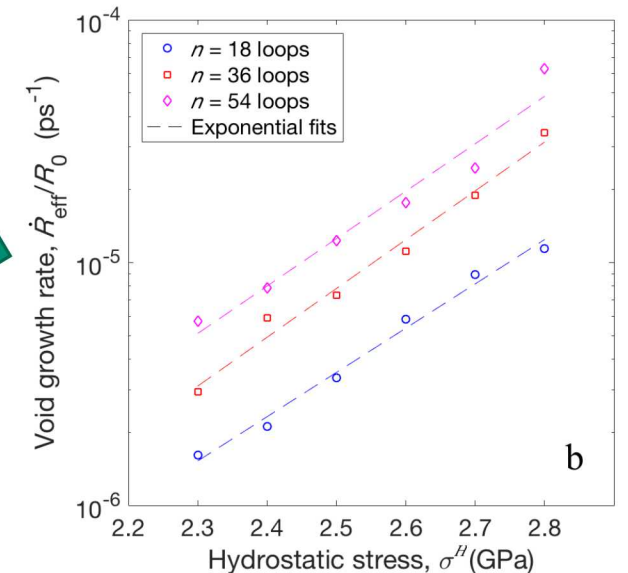
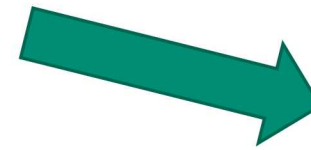
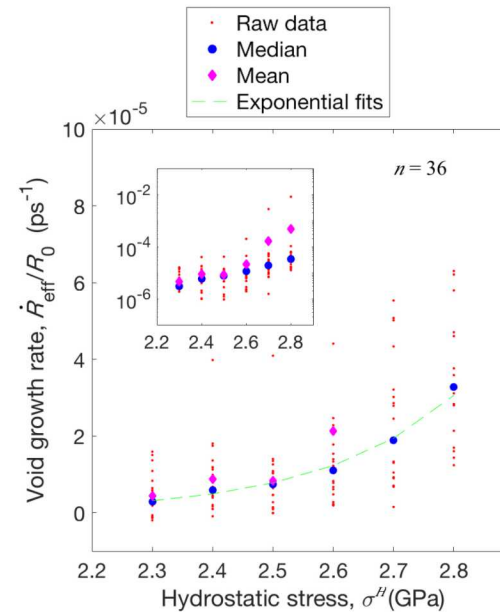
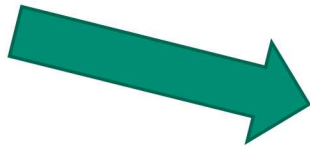
Can we make a meaningful comparison with Rice-Tracey?

- Can't do a one-to-one comparison because of boundary condition issues, but...

$$\frac{\dot{R}}{R} = \alpha \exp\left(\frac{3\sigma^H}{2\sigma_Y}\right) \dot{\epsilon}^{eq}$$



Repeat 20 times  
for each stress and  
dislocation density



Adsorption-mediated growth obeys exponential scaling!

$$\frac{\dot{R}}{R} = A(\rho) \exp(4.4\sigma^H)$$

Lower dislocation densities require higher hydrostatic stresses

- Recent experiments show that dynamic recrystallization in Al suppresses rupture (Noell et al., In Preparation)

Voids should exist in regions with enough dislocation content to accommodate growth

- Observe that voids most commonly appear in dislocation boundaries/walls

*Even in materials with inclusions*, local dislocation content will affect void nucleation/growth

Coupling adsorption-mediated growth with vacancy condensation (Cuitino and Ortiz, Acta Mater., 1995) may explain void nucleation in pure metals

Future work:

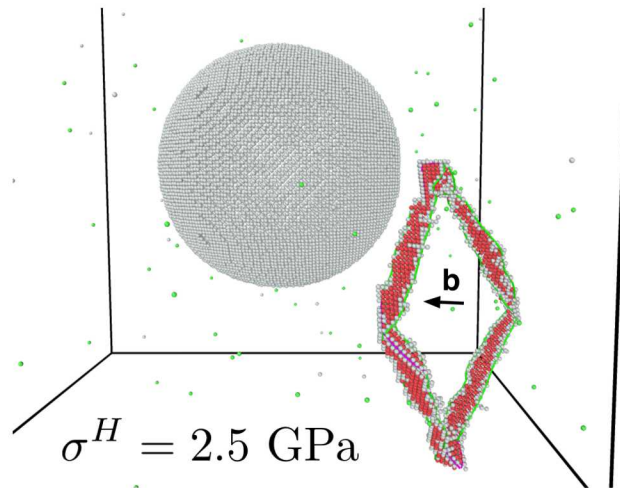
- Extend findings to lower stresses, lower dislocation densities – DDD collaboration with Wei Cai at Stanford
- Quantify influence of various dislocation processes (bulk cross-slip, surface cross-slip, glide, climb)



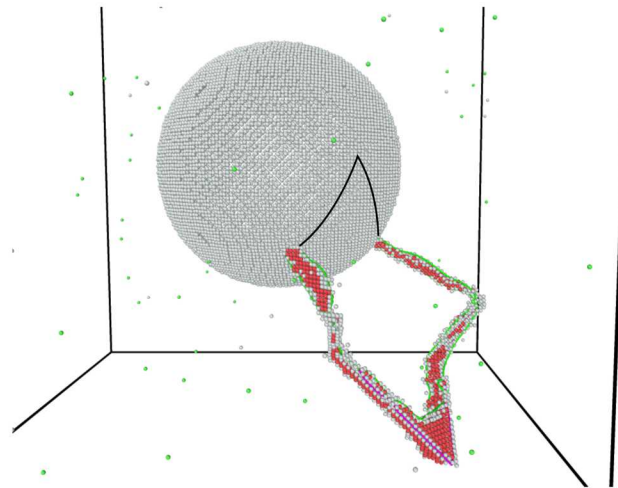


Back up slides

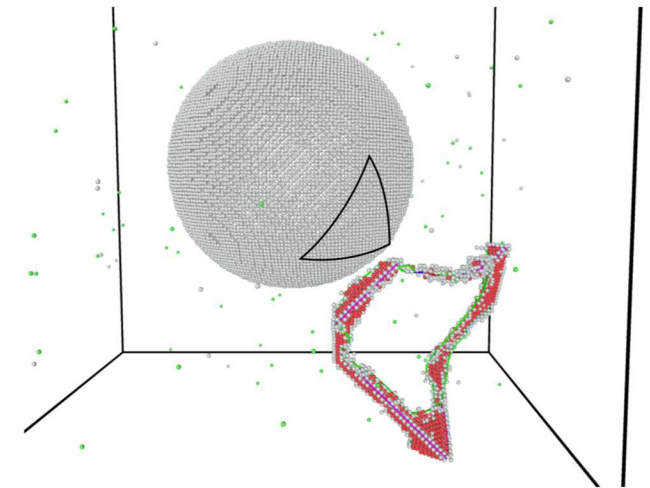




Prismatic loop in FCC Al



Glides towards and collides with void



Cross-slips, recombines, and glides away

Simulation with fixed number of atoms

